

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	(@ad<="19950130") and via and "etch stop" and "hard mask" and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:00
S2	11	(@ad<="19950130") and via and "etch stop" and "hard mask" and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:50
S3	2	("5328533").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:05
S4	2	("5328533").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:05
S5	19	(@ad<="19950130") and via and ("etch stop" or etchstop) and ("hard mask" or hardmask) and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:51
S6	8	(@ad<="19950130") and via and ("etch stop" or etchstop) and ("hard mask" or hardmask) and conductor not S2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:52
S7	21	(@ad<="19950130") and via and ("etch stop" or etchstop) and (fourth with (insulator or dielectric)) and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:53
S8	29	(@ad<="19950130") and via and ("etch stop" or etchstop) and (fourth with (insulat\$ or dielectric)) and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:53

S9	2	("5328553").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:50
S10	2	("20040175952").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:52
S11	5520	(@ad<="19950130") and (438/69\$.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:58
S12	428	(@ad<="19950130") and (438/69\$.ccls.) and via	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:58
S13	32	(@ad<="19950130") and (438/69\$.ccls.) and via and ("etch stop" or etchstop)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:59
S14	2	("5240871").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:13
S15	6673	(@ad<="19950130") and (nitride with etch\$3) same (oxide with etch\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:41
S16	906	(@ad<="19950130") and (nitride near2 etch\$3) same (oxide near2 etch\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:42

S17	641	((@ad<="19950130") and (nitride near2 etch\$3) with (oxide near2 etch\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:42
S18	2	("4385937").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:57
S19	215	((@ad<="19950130") and (nitride near2 etch\$3) with (oxide near2 etch\$3)) and (memory or storage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 17:20
S20	22	(Doan-Trung.in.) or ("Cathay- David.in")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:18
S21	402	((@ad<="19950130") and ("438"/\$.cls.) and via and ("etch stop" or etchstop)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:22
S22	99	((@ad<="19950130") and ("438"/\$.cls.) and via and ("etch stop" or etchstop) and (memory or storage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:23
S23	3	((@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (via or trench)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:20
S24	5	((@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (etch\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:28

S25	2	((@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (etch\$3) not S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:29
S26	0	((@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (damascene)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:32
S27	7	((@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) and (etch)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:33
S28	7	((@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) and (etch)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:33
S29	19	((@ad<="19950130") and (first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) and (etch\$3) and damascene	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:56
S30	126	((@ad<="19950130") and (storage or dram or memory) and alignment	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:18
S31	4	((@ad<="19950130") and (storage or dram or memory) and (alignment with (hole or via or contact))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:19

S32	8855	(@ad<="19950130") and (storage or dram or memory) and (aligned with (hole or via or contact))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:20
S33	689	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:21
S34	274	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and (first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) and (etch\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:24
S35	136	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) with (etch\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:25
S36	69	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat\$4 or isolat\$3)) with (second near2 (dielectric or insulat\$4 or isolat\$3)) with (etch\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:25
S37	18	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat\$4 or isolat\$3)) with (second near2 (dielectric or insulat\$4 or isolat\$3)) with (etch\$3) with (third near2 (dielectric or insulat\$4 or isolat\$3)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:26

S38	3	((@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat\$4 or isolat\$3)) with (second near2 (dielectric or insulat\$4 or isolat\$3)) with (etch\$3) with (third near2 (dielectric or insulat\$4 or isolat\$3))) and stop	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:28
S39	32	("4252840" "4758528" "4974040" "5150278" "5196910" "5240871" "5281549" "5292677" "5324681" "5328553" "5338700" "5476806" "5479054" "5502336" "5605857" "6744091").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 13:30
S40	2	("20040175952").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 14:50
S41	1	S40 and (fourth with insulation with side\$1wall with conductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 14:50

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